

2SK1579 Silicon N Channel MOS FET

REJ03G0956-0200 (Previous: ADE-208-1296) Rev.2.00 Sep 07, 2005

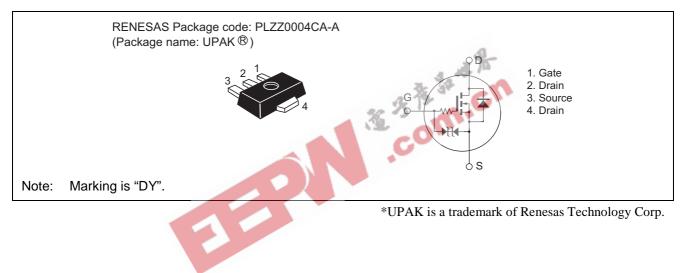
Application

High speed power switching

Features

- Low on-resistance
- High speed switching
- Suitable for low voltage operation

Outline





Absolute Maximum Ratings

			$(Ta = 25^{\circ}C)$	
Item	Symbol	Ratings	Unit	
Drain to source voltage	V _{DSS}	12	V	
Gate to source voltage	V _{GSS}	±7	V	
Drain current	ID	2	А	
Drain peak current	I _{D(pulse)} *1	4	А	
Body to drain diode reverse drain current	I _{DR}	2	А	
Channel power dissipation	Pch ^{*2}	1	W	
Channel temperature	Tch	150	°C	
Storage temperature	Tstg	-55 to +150	°C	

Notes: 1. PW \leq 100 µs, duty cycle \leq 10%

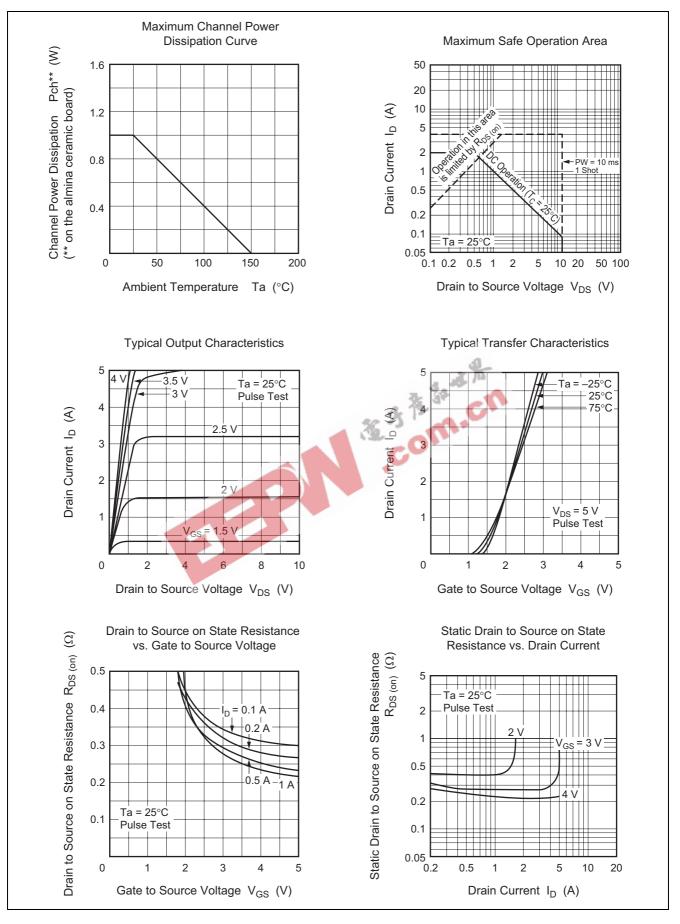
2. Value on the alumina ceramic board (12.5 \times 20 \times 0.7 mm)

Electrical Characteristics

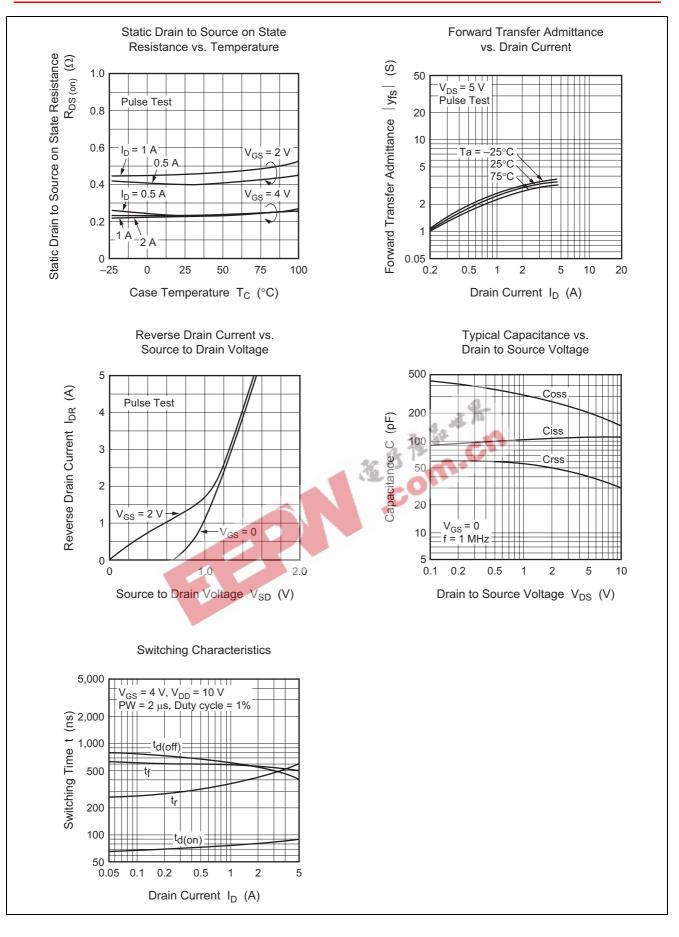
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Drain to source cutoff current	I _{DSS}	_	_	1	μΑ	$V_{DS} = 8 V, V_{GS} = 0$
Gate to source cutoff current	I _{GSS}	_	_	±5	μA	$V_{GS} = \pm 6.5 \text{ V}, V_{DS} = 0$
Gate to source cutoff voltage	V _{GS(off)}	0.4	_	1.4	V	$V_{DS} = 5 \text{ V}, \text{ I}_{D} = 100 \mu\text{A}$
Drain to source on resistance (1)	R _{DS(on)} 1	_	0.36	0.7	Ω	$V_{GS} = 2.2 \text{ V}, I_D = 0.5 \text{ A}^{*3}$
Drain to source on resistance (2)	R _{DS(on)} 2	-	0.25	0.35	Ω	$V_{GS} = 4 \text{ V}, \text{ I}_{D} = 1 \text{ A}^{*3}$
DC forward transfer admittance	y _{fs}	1	2.5	1 th	S	$V_{DS} = 5 V, I_D = 1 A,$
			· K	3	1.	ΔV_{GS} = 0.1 V ^{*3}
Input capacitance	Ciss	-	110	-0	pF	$V_{DS} = 5 V, V_{GS} = 0,$
Reverse transfer capacitance	Crss	-	30	6	pF	f = 1 MHz
Output capacitance	Coss		150	_	pF	
Turn-on time	t _(on)	77	500	_	ns	$I_D = 0.2 \text{ A}, V_{GS} = 0,$
Turn-off time	t _(off)		1500	_	ns	$Vin = 4 V, R_{L} = 51 \Omega^{*3}$
Note: 3. Pulse Test						



Main Characteristics

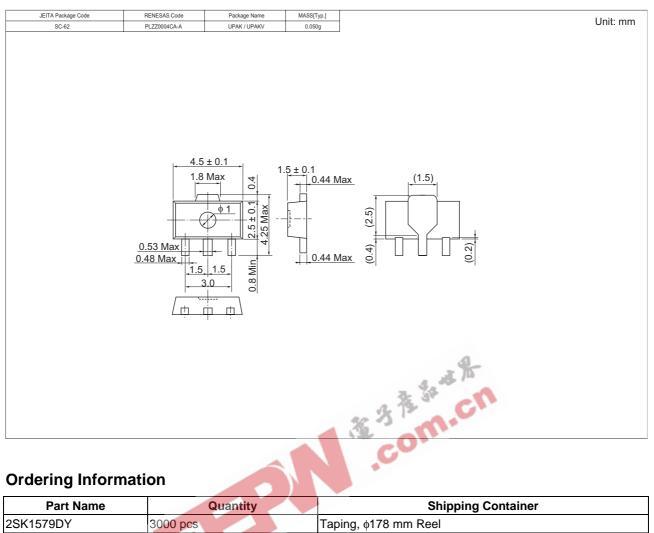








Package Dimensions



Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.



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Renesas Technology Malaysia Sdn. Bhd.

Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No.18, Jalan Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia Tel: <603> 7955-9390, Fax: <603> 7955-9510